

What is claimed is:

1. A semiconductor integrated circuit device comprising:
  - a first MOS transistor
    - having a first backgate region, a first conductive region, and a second conductive region, and
      - having the first backgate region and the first conductive region thereof connected together;
    - a second MOS transistor
      - having a second backgate region, a third conductive region, and a fourth conductive region,
        - having the second backgate region and the third conductive region thereof connected to the first backgate region and the first conductive region of the first MOS transistor, and
      - receiving at the fourth conductive region thereof a first direct-current voltage;
    - a voltage setting circuit
      - setting a second direct-current voltage fed to a gate of the second MOS transistor; and
    - an anti-reverse-current element
      - receiving the first direct-current voltage or a third direct-current voltage produced from the first direct-current voltage, and
        - connected to the voltage setting circuit in such a way as to prevent a reverse current from flowing through the voltage setting circuit,
  - wherein the voltage setting circuit produces, according to the first direct-

current voltage or the third direct-current voltage, the second direct-current voltage within a withstand voltage range of the second MOS transistor.

2. A semiconductor integrated circuit device as claimed in claim 1,  
wherein the first and second MOS transistors are of a same polarity.

3. A semiconductor integrated circuit device as claimed in claim 1,  
wherein the anti-reverse-current element is a diode.

4. A semiconductor integrated circuit device as claimed in claim 1,  
wherein the voltage setting circuit is composed of voltage-division resistors.

5. A semiconductor integrated circuit device comprising:  
a first MOS transistor of a P-channel type  
having a backgate and a first P-type diffusion layer thereof connected together;  
a second MOS transistor of a P-channel type  
having a backgate and a third P-type diffusion layer thereof connected to the backgate and the first P-type diffusion layer of the first MOS transistor, and receiving at a fourth P-type diffusion layer thereof a first direct-current voltage;

a voltage-division resistor circuit

having one end thereof grounded, and

feeding, as a second direct-current voltage, a division voltage

produced thereby to a gate of the second MOS transistor; and

a diode

receiving at an anode thereof the first direct-current voltage or a third direct-current voltage produced from the first direct-current voltage, and

having a cathode thereof connected to another end of the voltage-division resistor circuit,

wherein the second direct-current voltage from the voltage-division resistor circuit is kept within a withstand voltage range of the second MOS transistor according to the first direct-current voltage or the third direct-current voltage.